

With the defect repairing of the present invention, gallium ions are irradiated/injected at a specified position for a glass substrate corresponding to a defect remaining after digging of a trench into a Levenson mask using a focused ion beam apparatus, the glass substrate into which the gallium ions have been injected then being soaked in an alkaline solution so that portions impregnated with gallium ions are removed by dissolving in a localized manner.